(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
24 June 2004 (24.06.2004)

PCT

(10) International Publication Number
WO 2004/053926 A2

(51) International Patent Classification[7]: H01L

(21) International Application Number:
PCT/EP2003/050958

(22) International Filing Date: 8 December 2003 (08.12.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/318,605 11 December 2002 (11.12.2002) US

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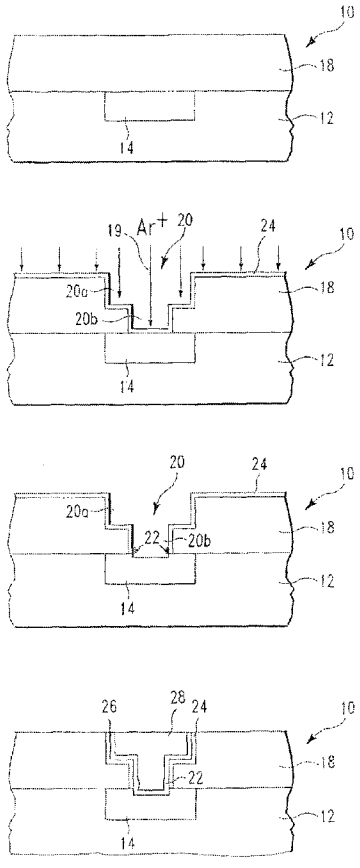
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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, MC, NL, PT, RO, SE, SI,

[Continued on next page]

(54) Title: A METHOD FOR DEPOSITING A METAL LAYER ON A SEMICONDUCTOR INTERCONNECT STRUCTURE



(57) Abstract: Disclosed is a method for depositing a metal layer on an interconnect structure for a semiconductor wafer. In the method, a metal conductor is covered by a dielectric layer. The dielectric layer is patterned so as to expose the metal conductor. A liner layer is then deposited into the pattern. The liner layer is then argon sputter etched to remove the liner layer and expose the metal conductor. In the process of argon sputter etching, the liner layer is redeposited onto the sidewall of the pattern. Lastly, an additional layer is deposited into the pattern and covers the redeposited liner layer.

WO 2004/053926 A2

SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report*

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